

Silicon PNP Power Transistors

2SB1227

DESCRIPTION

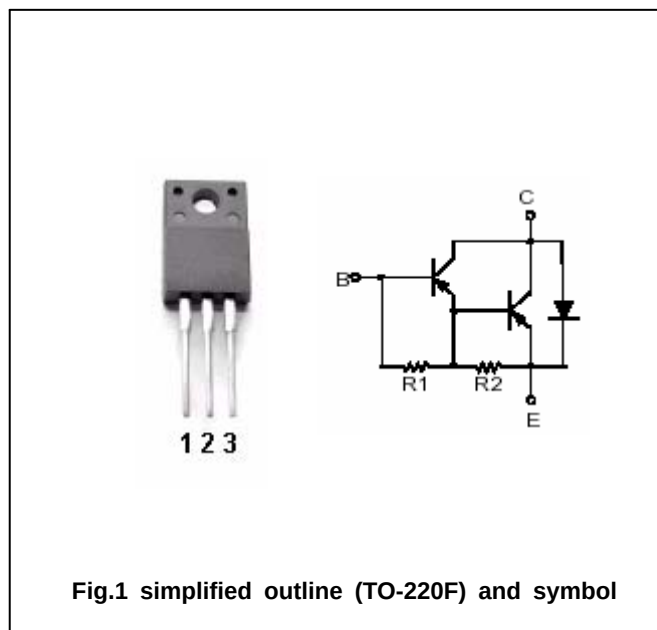
- With TO-220F package
- Complement to type 2SD1829
- High DC current gain.
- Large current capacity and wide ASO.
- Low saturation voltage.
- DARLINGTON

APPLICATIONS

- Suitable for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-5	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector dissipation	$T_C=25^\circ\text{C}$	25	W
		$T_a=25^\circ\text{C}$	2	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon PNP Power Transistors

2SB1227

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-5mA; I_E=0$	-110			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; R_{BE}=\infty$	-100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2.5A; I_B=-5mA$		-1.0	-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2.5A; I_B=-5mA$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V; I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-3.0	mA
h_{FE}	DC current gain	$I_C=-2.5A; V_{CE}=-3V$	1500	4000		
f_T	Transition frequency	$I_C=-2.5A; V_{CE}=-5V$		20		MHz

Switching times

t_{on}	Turn-on time	$I_C=500I_{B1}=-500I_{B2}=-2A$ $V_{CC}=-50V, R_L=25\Omega$		0.7		μs
t_{stg}	Storage time			1.3		μs
t_f	Fall time			1.5		μs

Silicon PNP Power Transistors

2SB1227

PACKAGE OUTLINE

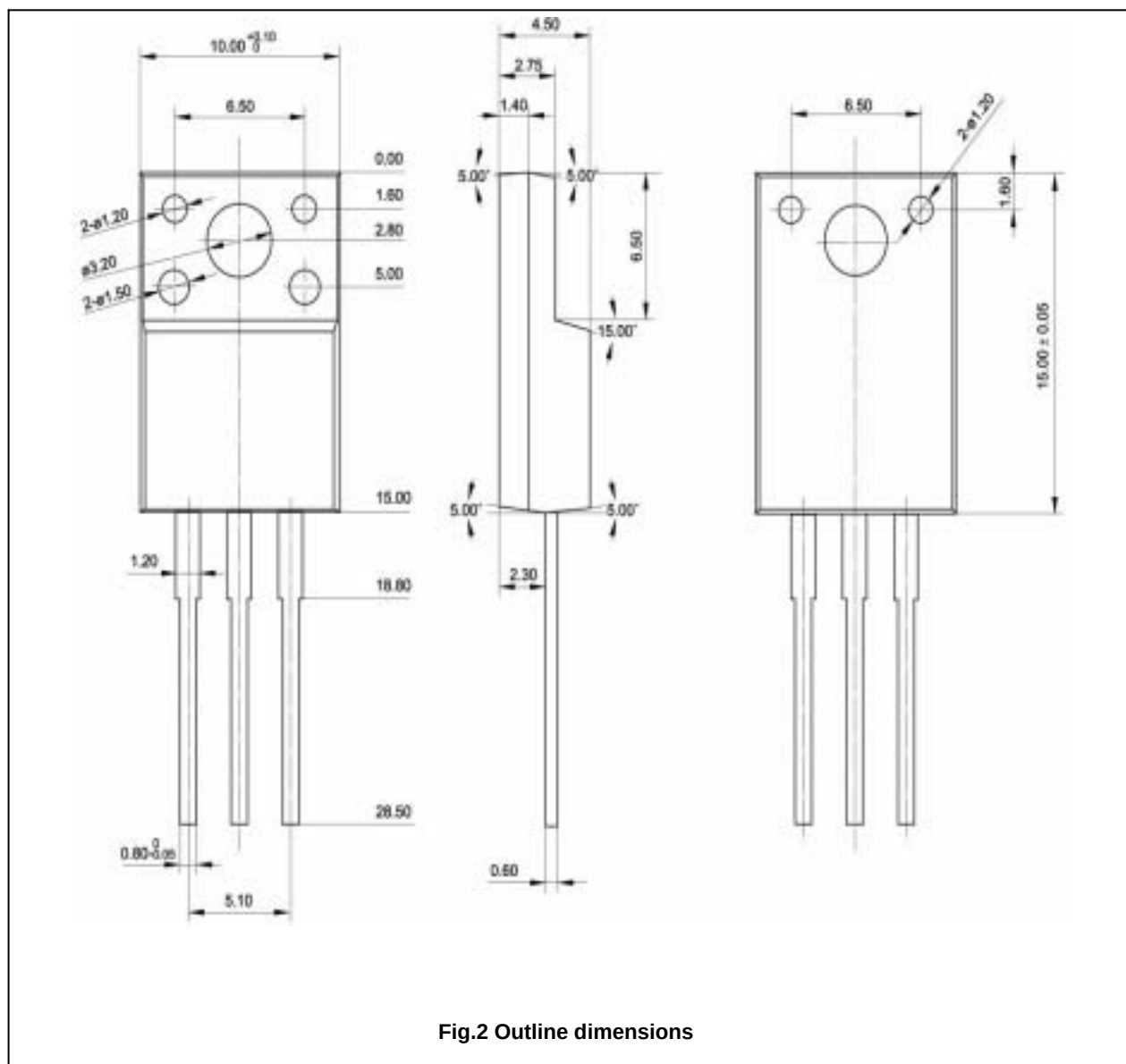


Fig.2 Outline dimensions